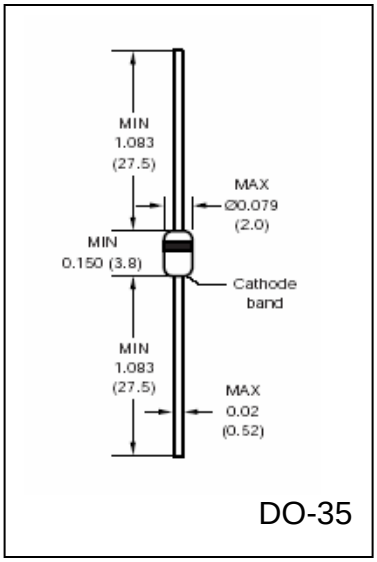
SWITCHING DIODE

1N4448

VOLTAGE RANGE **100 Volts**
CURRENT **150 mA**

FEATURES

- Silicon Expitaxial Planer Diode
- Fast Switching speed
- General purpose switching applications
- Also available in the MELF package as the LL4448



MECHANICAL DATA

- Case: DO-35
- Leads: Axial, solderable per MIL-STD-202 Method 208C
- Polarity: Color band denotes cathode end
- Weight: 0.0045 ounce, 0.13 gram, approx.

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

- Ratings at 25^{O}C ambient temperature unless otherwise specified

	SYMBOLS		UNIT
Non-Repetitive Peak Reverse Voltage	V_R	100	Volt
Maximum Repetitive Peak Reverse Voltage	V_{RM}	75	Volts
Forward Continuous Current	I_{FM}	500	mA
Non-Repetitive Peak Forward Aurge Current @ T = 1.0µS T = 1.0S	I_{FSM}	2.0 1.0	Amps
Maximum Forward Voltage @ 5.0mA 100mA	V_F	0.72 1.0	Volts
Maximum Leakage Current, (Note 1) @ V_R = 75V V_R = 70V, T_J = 150^{O}C V_R = 20V, T_J = 150^{O}C	I_R	5.0 50 30	µA
Maximum Reverse Recovery Time I_F = 10mA, I_R=10mA, I_{RR} = 1mA, R_L = 100Ω	t_{rr}	4	nS
Power dissipation (Note 1)	P_{TOT}	500	mW
Typical Junction Capacitance , V_F = 1V, f = 1MHz	C_J	4.0	pF
Typical Thermal Resistance	$R_{\theta JA}$	350	^{O}C/W
Operating Junction Temperature Range	T_J	(-65 to +175)	^{O}C
Storage Temperature Range	T_{STG}	(-65 to +175)	^{O}C

Notes:

1. Valid provided leads at a distance of 0.31” (8mm) from case are kept at ambient temperature

RATINGS AND CHARACTERISTIC CURVES 1N4448

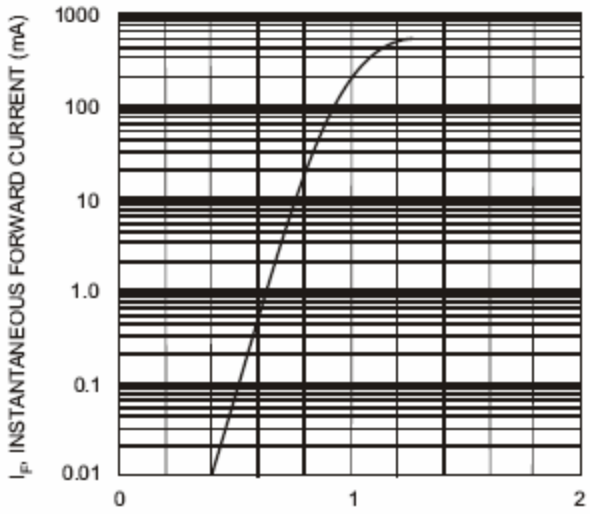


Fig. 1 Forward Characteristics

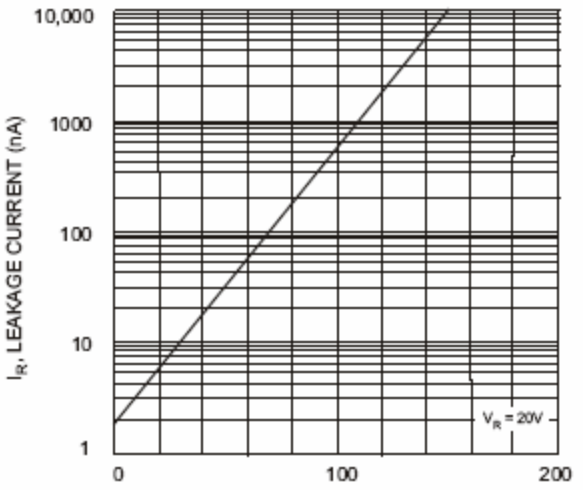


Fig. 2, Leakage Current vs Junction Temperature